# NSN 5961-01-092-4367

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## Inclosure Material:

Metal

## **Overall Length:**

Between 0.250 inches and 0.300 inches

## **Overall Diameter:**

Between 0.760 inches and 0.830 inches

# **Mounting Facility Quantity:**

2

## **Internal Configuration:**

Junction contact

## Electrode Internally-electrically Connected To Case:

Collector

## **Mounting Method:**

Unthreaded hole

Features Provided:

#### Hermetically sealed case

Semiconductor Material:

Silicon

## Voltage Rating In Volts Per Characteristic:

500.0 breakdown voltage, collector to emitter, sustained and 700.0 breakdown voltage, collector to emitter, with specified voltage

between base and emitter and 8.0  $\,$  emitter to base voltage,  $\,$  dc  $\,$ 

# **Current Rating Per Characteristic:**

Between 10.00 amperes source cutoff current and 50.00 amperes source cutoff current

## **Power Rating Per Characteristic:**

250.0 watts small-signal input power, common-collector absolute

## Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

## **Special Features:**

Junction pattern arrangement: npn

## **Terminal Type And Quantity:**

1 case and 2 pin

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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